

Please type a plus sign (+) inside this box → +

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 1

Complete if Known

Application Number	Continuation of 10/348,965
Filing Date	Herewith
First Named Inventor	Satoru TAKASE
Group Art Unit	Unknown
Examiner Name	Unknown
Attorney Docket Number	001701.00202

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Number	Kind Code ² (if known)				
MT		5,430,679		Hiltebeitel et al.	07/1995	365	200
		5,487,039		Sukegawa	01/23/1996	365	200
		5,495,447		Butler et al.	02-27-1996	365	200
		5,502,676		Pelley III, et al.	03/26/1996	365	200
		5,684,746		Oowaki, et al.	11/1997	365	200
MT		5,703,817		Shiratake, et al.	12/1997	365	200
		5,793,683		Evans	08-11-1998	365	200
		5,848,009		Lee et al.	12/1998	365	200
		5,862,080		Harari et al.	01-19-1999	365	185.29
		6,018,626		Zook	01-25-2000	703	24
MT		6,188,618		Takase	02/2001	365	200
		6,314,032		Takase	11/2001	365	200
		6,438,045		King et al.	08/2002	365	200
		6,542,420		Takase	4/2003	365	200
MT		2003/0081471	A1	Takase	5-1-2003	365	200

FOREIGN PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₂
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
MT		JP	4-102295	A	Fujitsu Ltd.	04-03-1992		
MT		JP	2-53299	A	Suzuki	02/1990		

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MT		Masahi Horiguchi et al., "A Flexible Redundancy Technique for High-Density DRAM's," Jan. 1991, IEEE Journal of Solid-State Circuits, Vol. 26, No. 1, pp. 12- 17.	
		Toshiaki Kiriata et al., "Fault-Tolerant Designs for 256 Mb DRAM," April 1996, IEEE Journal of Solid-State Circuits, Vol. 31, No. 4, pp. 558-566	
		Betty Prince, "Semiconductor Memories," 1983, Wisley, 2 nd Ed., pp. 761-762	
MT		Betty Prince, "Semiconductor Memories," 1983, Wisley, 2 nd Ed., pp. 762-764	

Examiner Signature	MT. TRAN	Date Considered	5/24/03
-----------------------	----------	--------------------	---------

¹EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.